

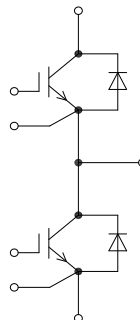
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2A200HB12C2F

Infineon Technologies

IGBT Modules

Any questions, please feel free to contact us.
info@kaimte.com



$V_{CES} = 1200V$
 $I_{C\ nom} = 200A / I_{CRM} = 400A$

典型应用

- 电机传动

电气特性

- 低开关损耗
- $T_{vj\ op} = 150^{\circ}C$

机械特性

- 铜基板

Typical Applications

- Motor drives

Electrical Features

- Low switching losses
- $T_{vj\ op} = 150^{\circ}C$

Mechanical Features

- Copper base plate

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: CU	date of publication: 2016-09-30	
approved by: MK	revision: V3.0	

IGBT, 逆变器 / IGBT, Inverter
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 95^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	200 294	A A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1\text{ ms}$	I_{CRM}	400	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	1100	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 200\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 200\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 200\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,85 2,20 2,30	2,25	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 6,60\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,20	5,80	6,40 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	1,40		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	3,7		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	11,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,47		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0,13 0,13 0,14		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,03 0,03 0,04		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0,30 0,38 0,40		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,05 0,07 0,08		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 5400\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{on}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	13,5 22,5 25,5		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3600\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{G\text{off}} = 0,62\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	12,5 20,0 22,5		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{S\text{CE}} \cdot di/dt$ $t_p \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	700		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{th\text{JC}}$		0,134	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{th\text{CH}}$	0,100		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

prepared by: CU	date of publication: 2016-09-30
approved by: MK	revision: V3.0

二极管, 逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1 \text{ ms}$	I_{FRM}	400	A
I^2t -值 I^2t - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	6400 5850	A^2s A^2s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,65 1,65 1,65	2,10	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 200 \text{ A}, -di_F/dt = 5400 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	190 200 205		A A A
恢复电荷 Recovered charge	$I_F = 200 \text{ A}, -di_F/dt = 5400 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	19,5 36,5 42,5		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 200 \text{ A}, -di_F/dt = 5400 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	8,00 14,5 16,5		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,203	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	0,133		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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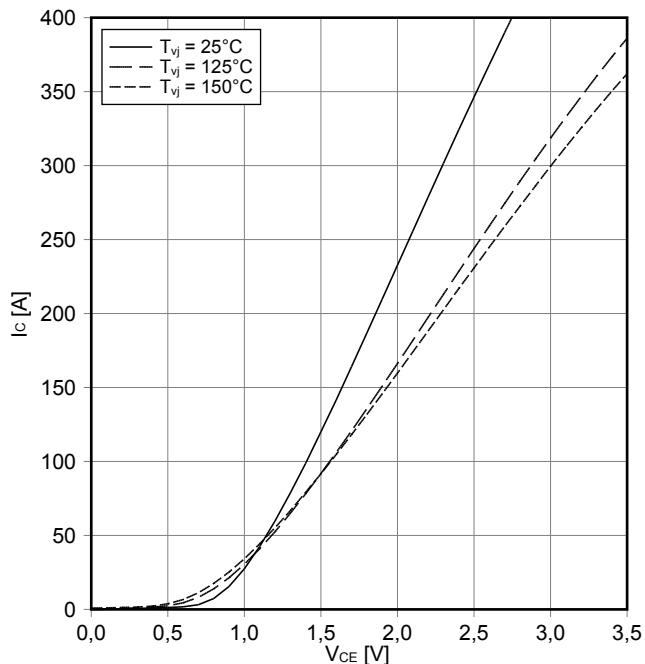
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		29,0 23,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		23,0 11,0		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
min. typ. max.					
杂散电感, 模块 Stray inductance module		L _{sCE}		20	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC+EE'}		0,70	mΩ
储存温度 Storage temperature		T _{stg}	-40	125	°C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00		6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	-	5,0 Nm
重量 Weight		G		285	g

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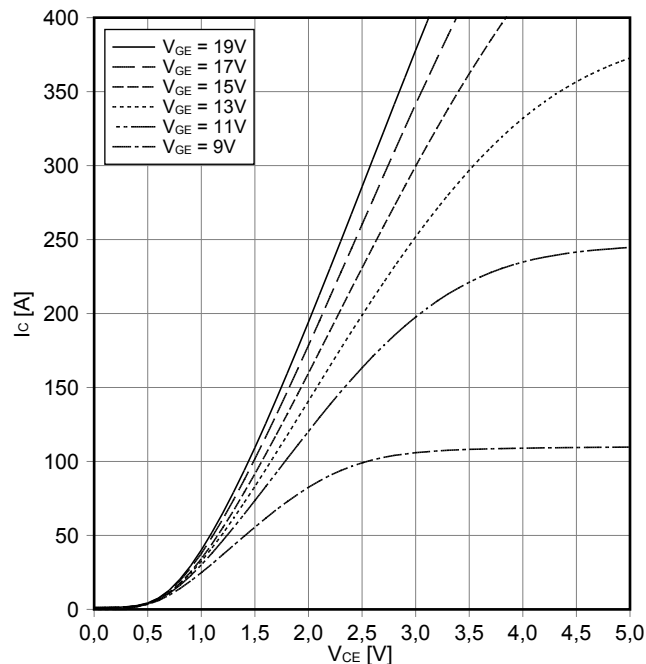
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



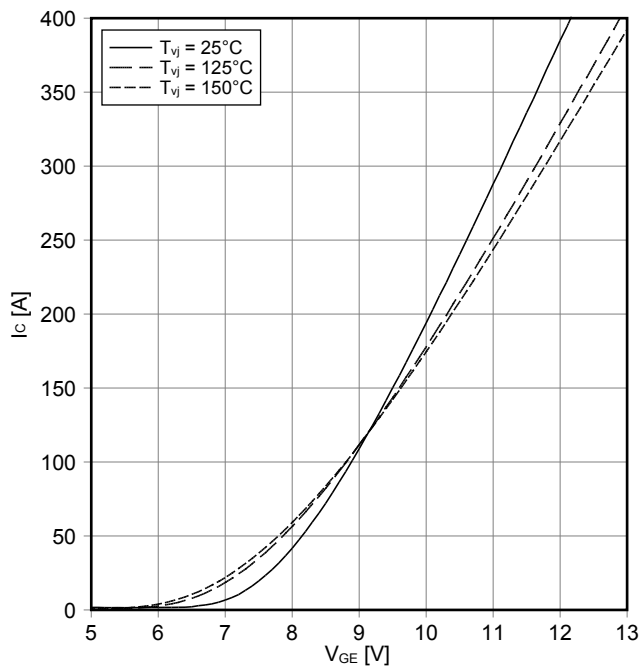
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



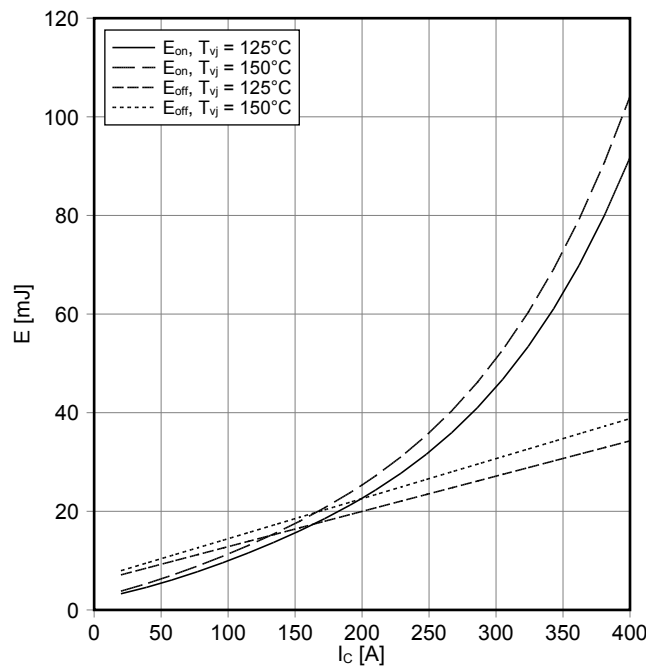
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

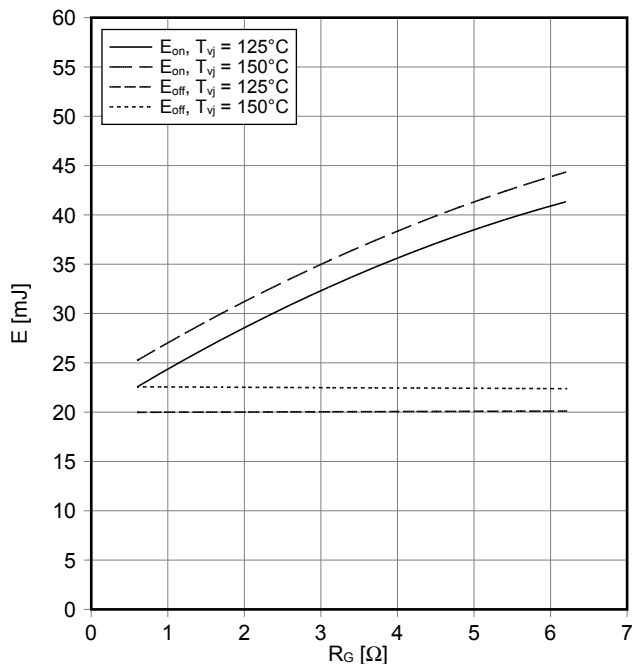
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.62\ \Omega$, $R_{Goff} = 0.62\ \Omega$, $V_{CE} = 600\text{ V}$



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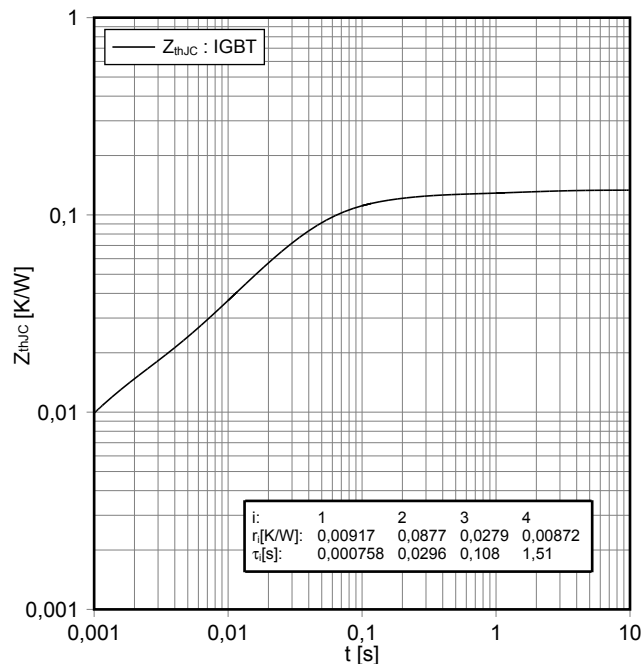
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 200\text{ A}, V_{CE} = 600\text{ V}$



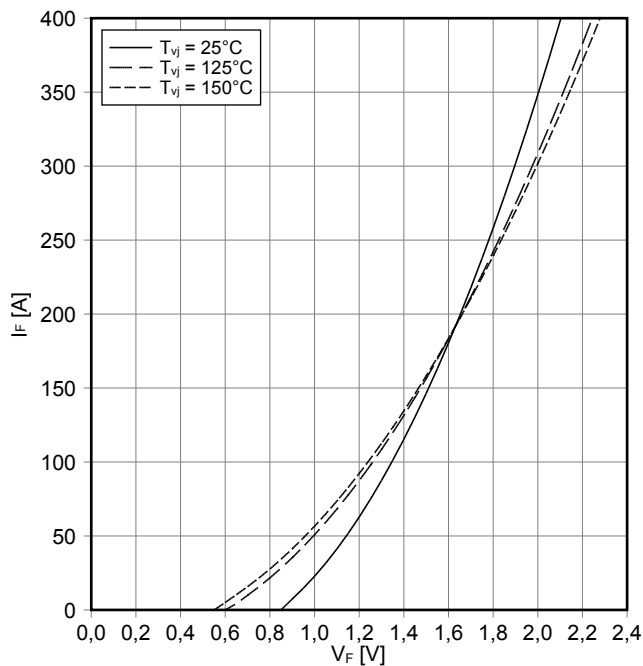
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



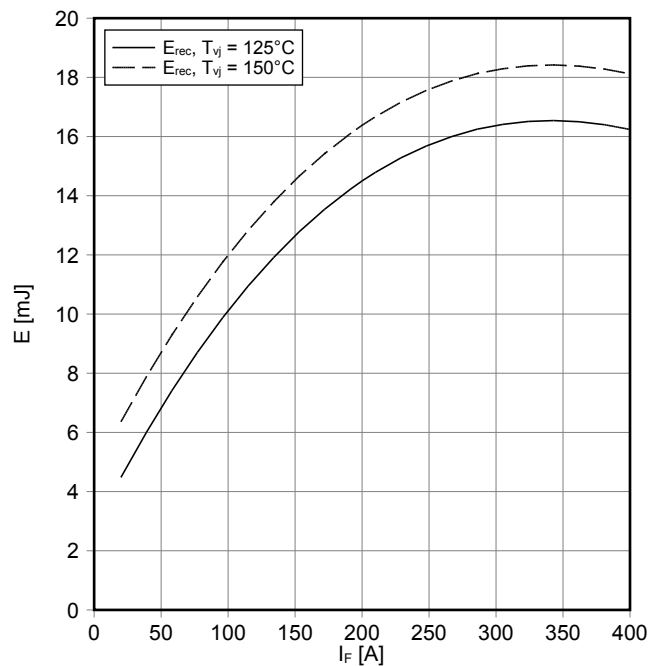
正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



开关损耗 二极管, 逆变器 (典型)
switching losses Diode, Inverter (typical)

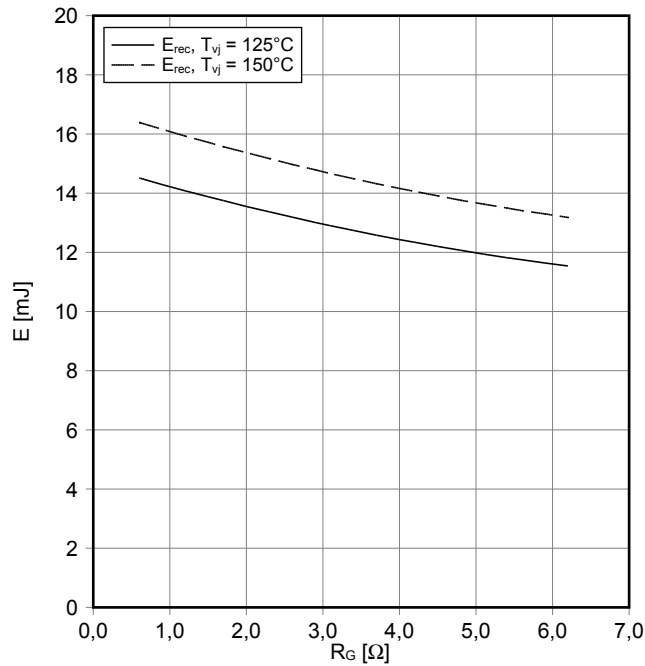
$E_{rec} = f(I_F)$
 $R_{Gon} = 0.62\ \Omega, V_{CE} = 600\text{ V}$



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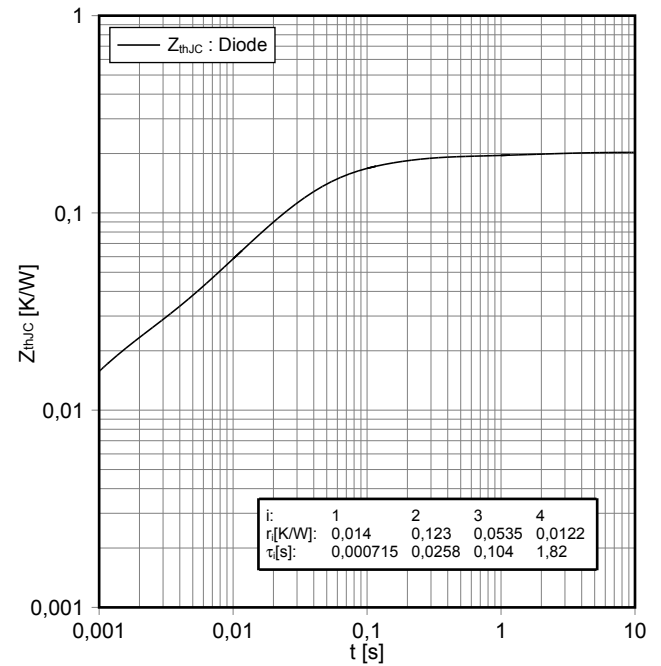
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 200\text{ A}, V_{CE} = 600\text{ V}$



瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

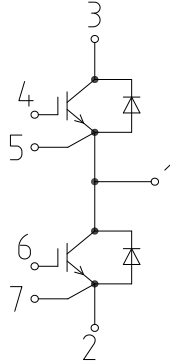
$Z_{thJC} = f(t)$



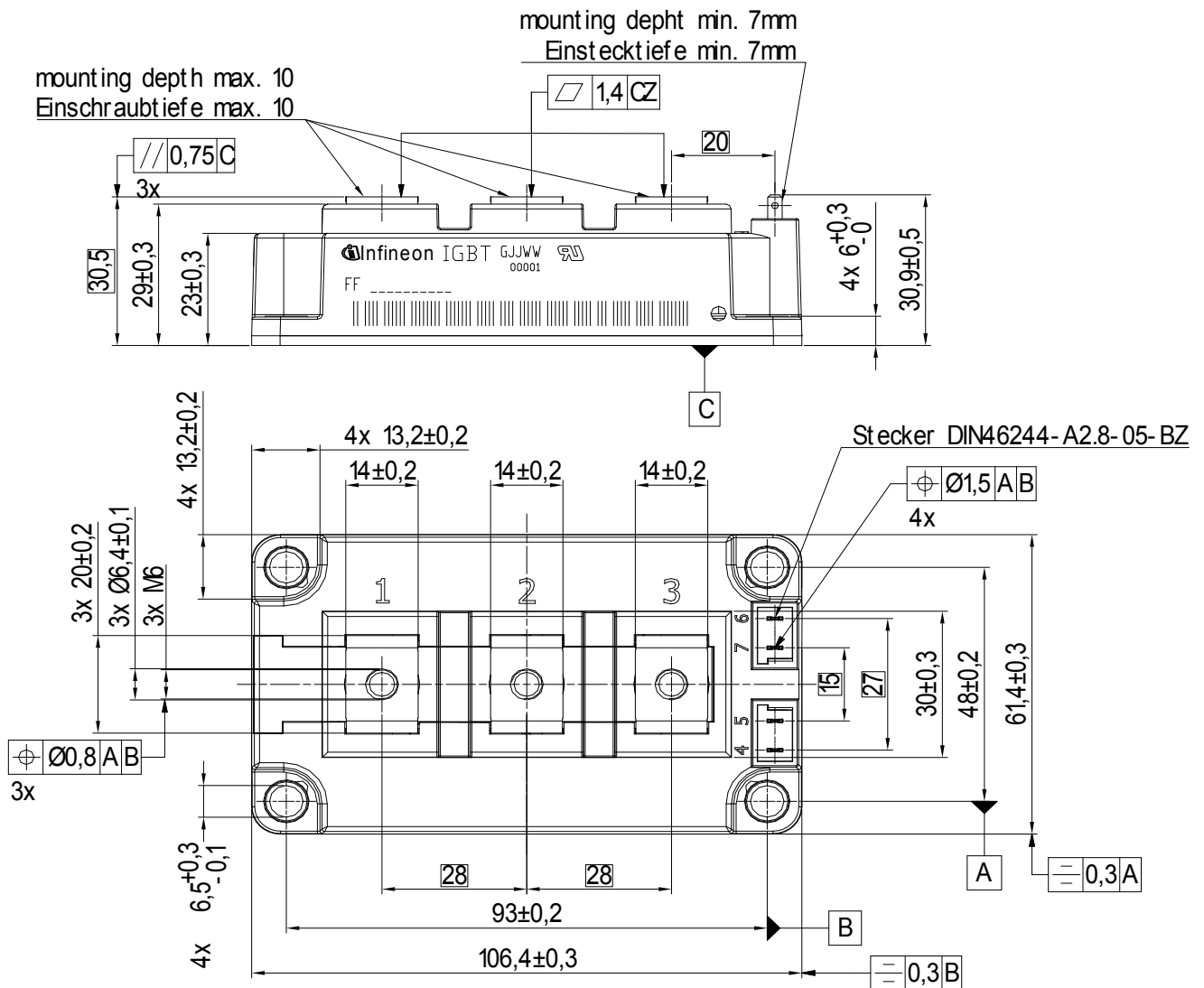
i:	1	2	3	4
r _i [K/W]:	0.014	0.123	0.0535	0.0122
τ _i [s]:	0.000715	0.0258	0.104	1.82

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approved by: MK	revision: V3.0

接线图 / Circuit diagram



封装尺寸 / Package outlines



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approved by: MK	revision: V3.0



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81726 München, Germany
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